

High power NPN epitaxial planar bipolar transistor

Features

- High breakdown voltage V_{CEO} = 140 V
- Complementary to 2STA1695
- Typical f_t = 20 MHz
- Fully characterized at 125 °C

Application

■ Audio power amplifier

Description

This device is an NPN transistor manufactured using BiT-LA (Bipolar transistor for linear amplifier) technology. The resulting transistor exhibits good gain linearity behavior. Recommended for 70 W to 100 W high fidelity audio frequency amplifier output stages.

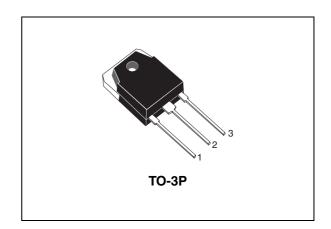


Figure 1. Internal schematic diagram

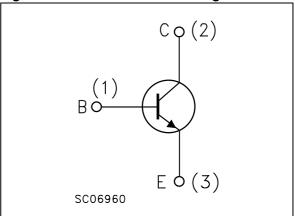


Table 1. Device summary

Order code	Marking	Package	Packaging
2STC4468	2STC4468	TO-3P	Tube

Electrical ratings 2STC4468

1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-base voltage (I _E = 0)	200	V
V _{CEO}	Collector-emitter voltage (I _B = 0)	140	V
V _{EBO}	Emitter-base voltage (I _C = 0)	6	V
Ic	Collector current	10	Α
I _{CM}	Collector peak current (t _P < 5 ms)	20	Α
P _{tot}	Total dissipation at T _c = 25 °C	100	W
T _{stg}	Storage temperature	-65 to 150	°C
T _J	Max. operating junction temperature	150	°C

Table 3. Thermal data

Symbol	Parameter	Value	Unit
R _{thj-case}	Thermal resistance junction-case max	1.25	°C/W
R _{thj-amb}	Thermal resistance junction-ambient max	35.7	°C/W

2 Electrical characteristics

 $(T_{case} = 25 \, ^{\circ}C; \text{ unless otherwise specified})$

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Тур.	Max.	Unit
I _{CBO}	Collector cut-off current (I _E = 0)	V _{CB} = 200 V			0.1	μΑ
I _{EBO}	Emitter cut-off current (I _C = 0)	V _{EB} = 6 V			0.1	μΑ
V _{(BR)CEO} ⁽¹⁾	Collector-emitter breakdown voltage (I _B = 0)	I _C = 50 mA	140			V
V _{(BR)CBO}	Collector-base breakdown voltage (I _E = 0)	I _C = 100 μA	200			V
V _{(BR)EBO} ⁽¹⁾	Emitter-base breakdown voltage (I _C = 0)	I _E = 1 mA	6			V
V _{CE(sat)} ⁽¹⁾	Collector-emitter saturation voltage	$I_C = 5 \text{ A}$ $I_B = 500 \text{ mA}$ $I_C = 7 \text{ A}$ $I_B = 700 \text{ mA}$			0.5 0.7	V V
V _{BE}	Base-emitter voltage	V _{CE} = 5 V I _C = 5 A			1.3	V
h _{FE}	DC current gain	$I_C = 3 A$ $V_{CE} = 4 V$ $I_C = 5 A$ $V_{CE} = 4 V$	70 50		140	
f _T	Transition frequency	$I_C = 0.5 \text{ A}$ $V_{CE} = 12 \text{ V}$		20		MHz
C _{CBO}	Collector-base capacitance (I _E = 0)	V _{CB} = 10 V f = 1 MHz		150		pF
	Resistive Load					
t _{on}	Turn-on time	$V_{CC} = 60 \text{ V}$ $I_{C} = 5 \text{ A}$		0.22		μs
t _{stg}	Storage time	$I_{B1} = -I_{B2} = 0.5 \text{ A}$		4.3		μs
t _f	Fall time			0.5		μs

^{1.} Pulse duration = 300 μ s, duty cycle \leq 1.5 %

Electrical characteristics 2STC4468

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

Figure 3. Power derating versus temperature

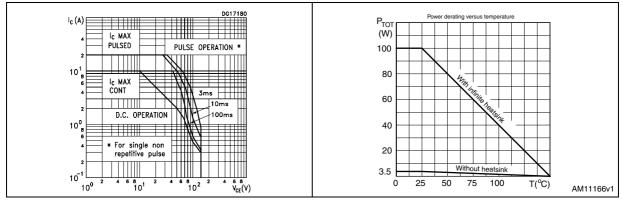


Figure 4. Output characteristics

Figure 5. DC current gain

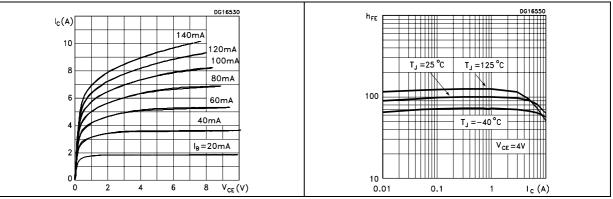


Figure 6. Collector-emitter saturation voltage Figure 7. Base-emitter voltage

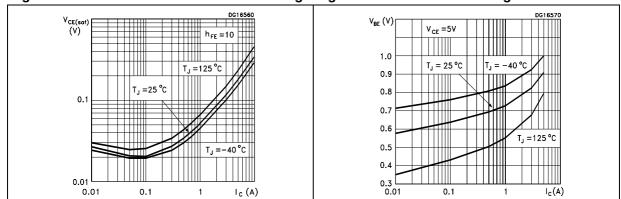
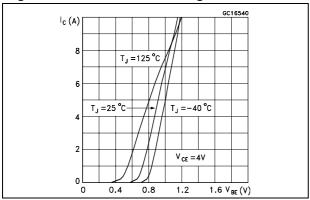
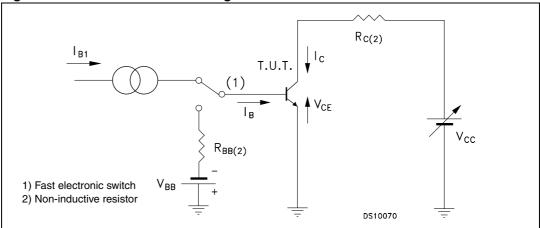


Figure 8. Base-emitter voltage



2.2 Test circuit

Figure 9. Resistive load switching test circuit



3 Package mechanical data

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Table 5. TO-3P mechanical data

Dim.	mm			
	Min.	Тур.	Max	
A	4.60		5	
A1	1.45	1.50	1.65	
A2	1.20	1.40	1.60	
b	0.80	1	1.20	
b1	1.80		2.20	
b2	2.80		3.20	
С	0.55	0.60	0.75	
D	19.70	19.90	20.10	
D1		13.90		
E	15.40		15.80	
E1		13.60		
E2		9.60		
е	5.15	5.45	5.75	
L	19.50	20	20.50	
L1		3.50		
L2	18.20	18.40	18.60	
øΡ	3.10		3.30	
Q		5		
Q1		3.80		

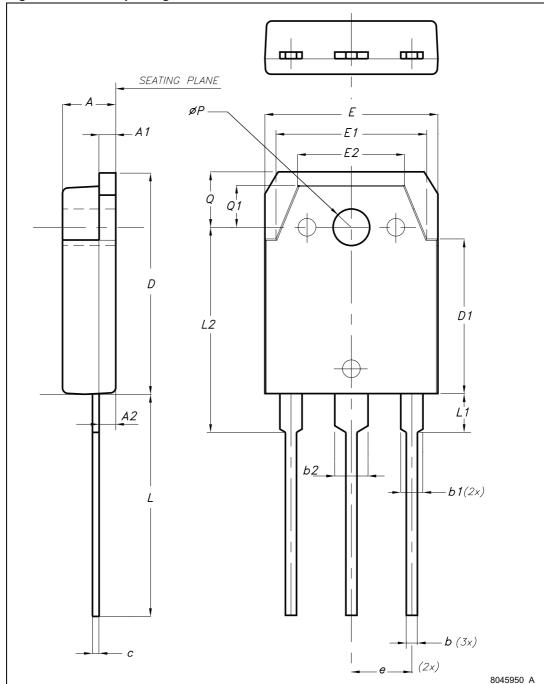


Figure 10. TO-3P package dimensions

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2STC4468 Revision history

4 Revision history

Table 6. Document revision history

Date	Revision	Changes
21-May-2007	1	Initial release
07-Nov-2008	2	Document status promoted from preliminary data to datasheet.
08-Feb-2012	3	Figure 3 insertedMechanical data updated

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